

May 2014

# FDMS86163P

# P-Channel PowerTrench® MOSFET

-100 V, -50 A, 22 mΩ

### **Features**

- Max  $r_{DS(on)}$  = 22 m $\Omega$  at  $V_{GS}$  = -10 V,  $I_D$  = -7.9 A
- Max  $r_{DS(on)}$  = 30 m $\Omega$  at  $V_{GS}$  = -6 V,  $I_D$  = -5.9 A
- Very low RDS-on mid voltage P-channel silicon technology optimised for low Qg
- This product is optimised for fast switching applications as well as load switch applications
- 100% UIL tested
- RoHS Compliant

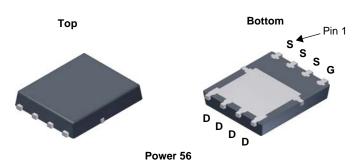


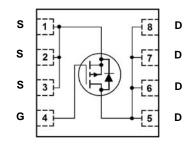
## **General Description**

This P-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

## **Applications**

- Active Clamp Switch
- Load Switch





## MOSFET Maximum Ratings T<sub>A</sub> = 25 °C unless otherwise noted

Symbol	Paramete		Ratings	Units	
V <sub>DS</sub>	Drain to Source Voltage			-100	V
$V_{GS}$	Gate to Source Voltage			±25	V
	Drain Current -Continuous	T <sub>C</sub> = 25 °C		-50	
$I_D$	-Continuous	T <sub>A</sub> = 25 °C	(Note 1a)	-7.9	Α
	-Pulsed		(Note 4)	-100	
E <sub>AS</sub>	Single Pulse Avalanche Energy		(Note 3)	486	mJ
В	Power Dissipation	T <sub>C</sub> = 25 °C		104	W
$P_{D}$	Power Dissipation	T <sub>A</sub> = 25 °C	(Note 1a)	2.5	VV
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperatur	e Range		-55 to +150	°C

### **Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.2	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	C/VV

## **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS86163P	FDMS86163P	Power 56	13 "	12 mm	3000 units

## **Electrical Characteristics** T<sub>J</sub> = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	cteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = -250 \mu A, V_{GS} = 0 V$	-100			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D$ = -250 $\mu$ A, referenced to 25 °C		-59		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -80 V, V <sub>GS</sub> = 0 V			-1	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = -250 \mu A$	-2	-2.8	-4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D$ = -250 $\mu$ A, referenced to 25 °C		6.2		mV/°C
	$V_{GS} = -10 \text{ V}, I_D = -7.9 \text{ A}$		17.8	22		
r <sub>DS(on)</sub>	r <sub>DS(on)</sub> Static Drain to Source On Resistance	$V_{GS} = -6 \text{ V}, I_D = -5.9 \text{ A}$		21.3	30	mΩ
		$V_{GS} = -10 \text{ V}, I_D = -7.9 \text{ A}, T_J = 125 ^{\circ}\text{C}$		29	36	
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -7.9 A		29		S

## **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance			3070	4085	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = -50 V, V <sub>GS</sub> = 0 V, f = 1 MHz		501	670	рF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1 1/11/12		21	35	pF
R <sub>q</sub>	Gate Resistance		0.1	2.6	5.3	Ω

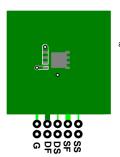
## **Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time		17	30	ns
t <sub>r</sub>	Rise Time	V <sub>DD</sub> = -50 V, I <sub>D</sub> = -7.9 A,	8.8	18	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = -10 \text{ V}, R_{GEN} = 6 \Omega$	33	53	ns
t <sub>f</sub>	Fall Time		6.9	14	ns
$Q_g$	Total Gate Charge	V <sub>GS</sub> = 0 V to -10 V	42	59	nC
Qg	Total Gate Charge	$V_{GS} = 0 \text{ V to -6 V}$ $V_{DD} = -50 \text{ V},$	26	37	nC
Q <sub>gs</sub>	Gate to Source Charge	I <sub>D</sub> = -7.9 A	11.8		nC
$Q_{gd}$	Gate to Drain "Miller" Charge		7.1		nC

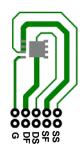
### **Drain-Source Diode Characteristics**

Vob Source to Drain Diode Forward Voltage	Source to Drain Diode, Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = -7.9 \text{ A}$ (Note 2)	)	-0.81	-1.3	V
	$V_{GS} = 0 \text{ V}, I_{S} = -2 \text{ A}$ (Note 2)	)	-0.75	-1.2	V	
t <sub>rr</sub>	Reverse Recovery Time	I <sub>E</sub> = -7.9 A, di/dt = 100 A/μs		63	102	ns
Q <sub>rr</sub>	Reverse Recovery Charge	r <sub>F</sub> = -7.9 A, αι/αι = 100 A/μs		132	210	nC

<sup>&</sup>lt;sup>1 No.</sup> 1. R<sub>0JA</sub> is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R<sub>0JC</sub> is guaranteed by design while R<sub>0CA</sub> is determined by the user's board design.



a) 50 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b) 125 °C/W when mounted on a minimum pad of 2 oz copper.

- 2. Pulse Test: Pulse Width < 300  $\mu$ s, Duty cycle < 2.0%. 3. Starting T $_J$  = 25 °C; P-ch: L = 3 mH, I $_{AS}$  = -18 A, V $_{DD}$  = -100 V, V $_{GS}$  = -10 V. 100% test at L = 0.1 mH, I $_{AS}$  = -58 A.
- 4. Pulse Id refers to Figure.11 Forward Bias Safe Operation Area.

## Typical Characteristics T<sub>J</sub> = 25 °C unless otherwise noted

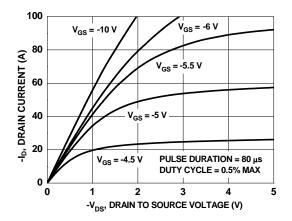


Figure 1. On Region Characteristics

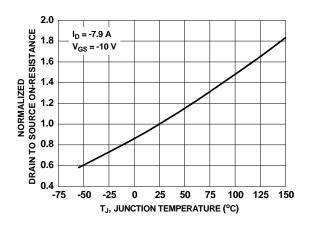


Figure 3. Normalized On Resistance vs Junction Temperature

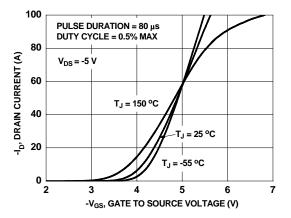


Figure 5. Transfer Characteristics

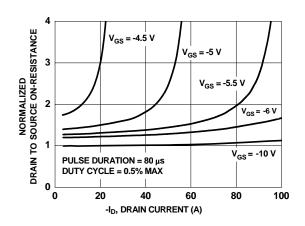


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

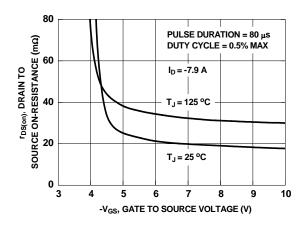


Figure 4. On-Resistance vs Gate to Source Voltage

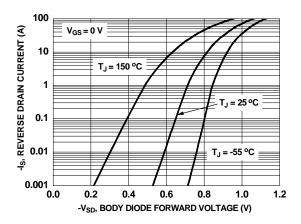


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

## **Typical Characteristics** $T_J = 25$ °C unless otherwise noted

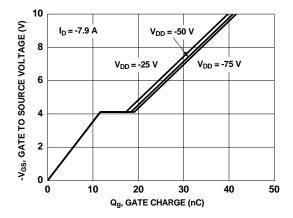


Figure 7. Gate Charge Characteristics

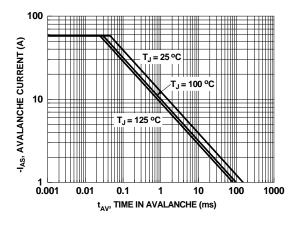


Figure 9. Unclamped Inductive Switching Capability

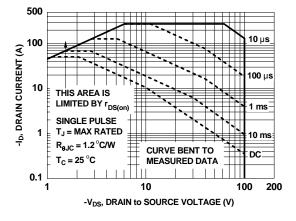


Figure 11. Forward Bias Safe Operating Area

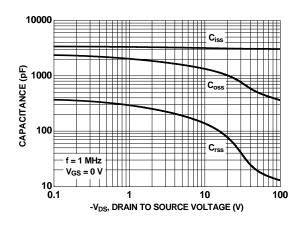


Figure 8. Capacitance vs Drain to Source Voltage

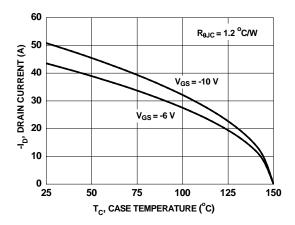


Figure 10. Maximum Continuous Drain Current vs Case Temperature

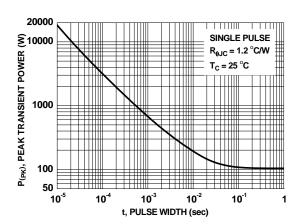


Figure 12. Single Pulse Maximum Power Dissipation

## **Typical Characteristics** T<sub>J</sub> = 25 °C unless otherwise noted

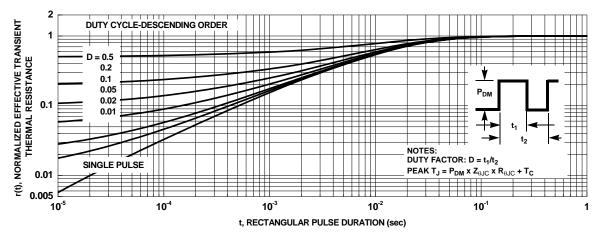
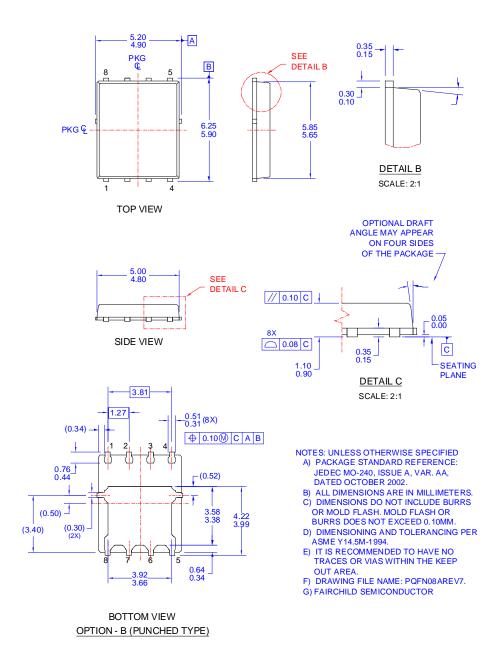


Figure 13. Junction-to-Case Transient Thermal Response Curve

## **Dimensional Outline and Pad Layout**



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